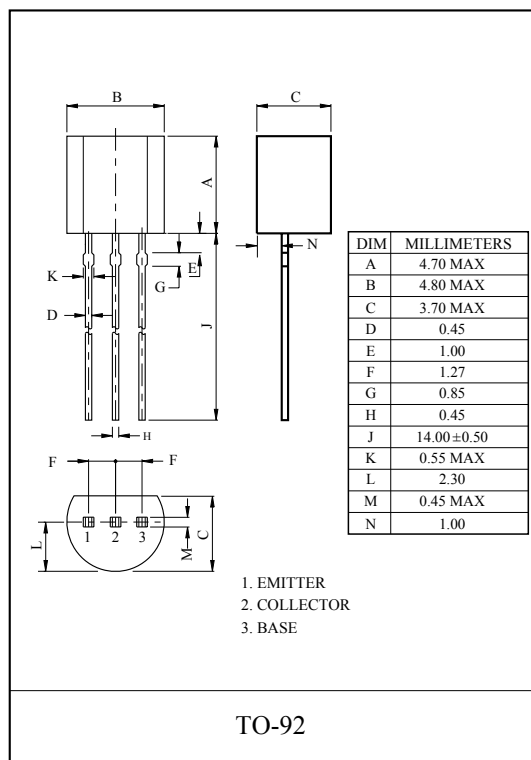


HIGH VOLTAGE APPLICATION.  
TELEPHONE APPLICATION.

## MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-300	V
Collector-Emitter Voltage	$V_{CEO}$	-300	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current	$I_C$	-500	mA
Emitter Current	$I_E$	500	mA
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_j$	150	℃
Storage Temperature	$T_{stg}$	-55 ~ 150	℃



## ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-300	-	-	$\mu A$
Emitter Cut-off Current	$V_{(BR)CEO}$	$I_C = -1.0mA, I_B = 0$	-300	-	-	$\mu A$
DC Current Gain	$h_{FE}^*$	$I_C = -1.0mA, V_{CE} = -10V$	25	-	-	
		$I_C = -10mA, V_{CE} = -10V$	40	-	-	
		$I_C = -30mA, V_{CE} = -10V$	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C = -20mA, I_B = -2.0mA$	-	-	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C = -20mA, I_B = -2.0mA$	-	-	-0.9	V
Transition Frequency	$f_T$	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	50	-	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -20V, I_E = 0, f = 1MHz$	-	-	6.0	V

Note : \* Pulse test :  $PW \leq 300\mu S, \text{ Duty Cycle} \leq 2\%$